





0.5A SBR[®] SURFACE MOUNT SUPER BARRIER RECTIFIER

Features

- Ultra Low Forward Voltage Drop
- Superior Reverse Avalanche Capability
- Patented Super Barrier Rectifier Technology
- Soft, Fast Switching Capability
- 150°C Operating Junction Temperature
- Lead Free by Design, RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: DFN1006H4-2
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: Cathode Dot
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.001 grams (approximate)



Bottom Viev

Maximum Ratings @T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _{RM}	20	>
RMS Reverse Voltage	V _{R(RMS)}	14	V
Average Rectified Output Current (See Figure 1)	I _O	500	mA
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load	I _{FSM}	6	А

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance (Note 3)	$R_{\theta JA}$	224	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-65 to +150	°C

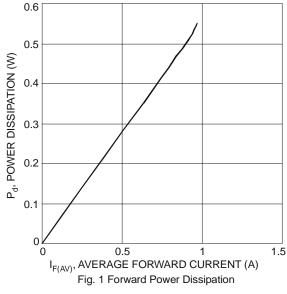
Electrical Characteristics @T_A = 25°C unless otherwise specified

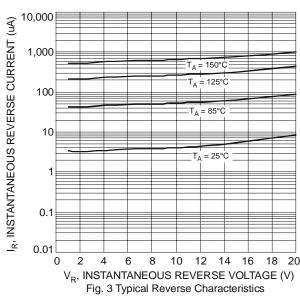
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 4)	V _{(BR)R}	20	-	-	V	I _R = 50μA
	VF	-	0.34	0.38		$I_F = 0.1A, T_j = 25^{\circ}C$
			0.25	0.28		$I_F = 0.1A, T_j = 150$ °C
Forward Valtage Dran			0.38	0.42		$I_F = 0.2A, T_j = 25^{\circ}C$
Forward Voltage Drop			0.31	0.34		$I_F = 0.2A, T_j = 150^{\circ}C$
			0.47	0.50		$I_F = 0.5A, T_i = 25^{\circ}C$
			0.42	0.45		I _F = 0.5A, T _j = 150°C
Lookaga Current (Note 4)	I _R	-	6	50	μΑ	$V_R = 20V, T_j = 25^{\circ}C$
Leakage Current (Note 4)			1.5	5	mA	$V_R = 20V, T_j = 150^{\circ}C$

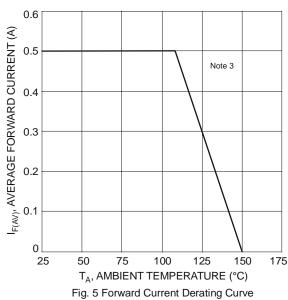
Notes

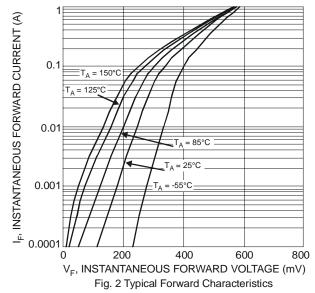
- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 3. Device mounted on FR-4 substrate. 2" x 2" 2oz. Copper, single sided PCB board.
- 4. Short duration pulse test used to minimize self-heating effect.











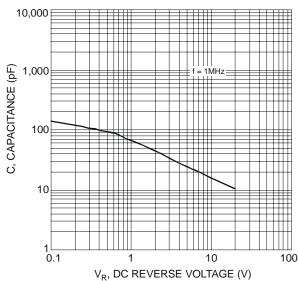
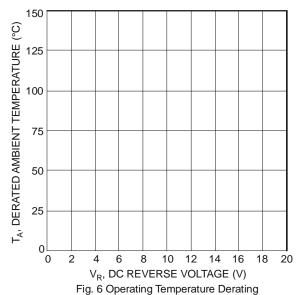


Fig. 4 Total Capacitance vs. Reverse Voltage





Ordering Information (Note 5)

Part Number	Case	Packaging
SBR05U20LPS-7	DFN1006H4-2	3000/Tape & Reel

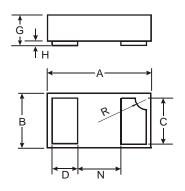
Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

• <u>5</u> 2

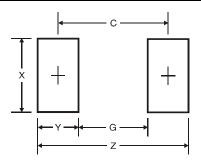
 $\underline{5}$ $\overline{2}$ = Product Type Marking Code Dot Denotes Cathode Side

Package Outline Dimensions



DFN1006H4-2				
Dim	Min	Max	Тур	
Α	0.95	1.075	1.00	
В	0.55	0.675	0.60	
၁	0.45	0.55	0.50	
D	0.20	0.30	0.25	
O	0.34	0.4	0.37	
H 0		0.05	0.03	
N —		_	0.40	
R	0.05	0.15	0.10	
All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.1
G	0.3
X	0.7
Y	0.4
С	0.7

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